ABSTRACT

AREA ARRAY AIR GAP STRUCTURE FOR INTERMETAL DIELECTRIC APPLICATION

A new method of forming air gaps between adjacent conducting lines of a semiconductor circuit by using a "holes everywhere" or a "reverse metal holes" mask that can be used to create holes in a dielectric layer. The dielectric that is being etched has been deposited across conducting lines, the holes that are being formed in this manner are closed by depositing a dielectric across the top of the holes. The holes can be etched across the entire layer of the deposited dielectric or can be etched in between the conducting lines.

(FIGURE 1 IS SUGGESTED FOR PUBLICATION)